

# SL02 to SL04

### **Vishay Semiconductors**

# **Small Surface Mount Schottky Diodes**

### Features

- For surface mounted applications
- Low-profile package
- Ideal for automated placement
- Low power loss, high efficiency
- High temperature soldering: 260 °C/10 seconds at terminals

### **Mechanical Data**

**Case:** JEDEC DO-219-AB (SMF) Plastic case **Polarity:** Color band denotes cathode end

Weight: approx. 0.01g



Packaging codes-options:

17249

G1-10 K per 13 " reel (8 mm tape), 50 K/box G2-3 K per 7 " reel (8 mm tape), 30 K/box

## **Parts Table**

Part	Type differentiation	Marking	Package
SL02	Single Diodes	S2	SMF
SL03	Single Diodes	S3	SMF
SL04	Single Diodes	S4	SMF

### **Absolute Maximum Ratings**

 $T_{amb} = 25 \ ^{\circ}C$ , unless otherwise specified

Parameter	Test condition	Part	Symbol	Value	Unit
Maximum repetitive peak reverse voltage		SL02	V <sub>RRM</sub>	20	V
		SL03	V <sub>RRM</sub>	30	V
		SL04	V <sub>RRM</sub>	40	V
Maximum RMS voltage		SL02	V <sub>RMS</sub>	14	V
		SL03	V <sub>RMS</sub>	21	V
		SL04	V <sub>RMS</sub>	28	V
Maximum DC blocking voltage		SL02	V <sub>DC</sub>	20	V
		SL03	V <sub>DC</sub>	30	V
		SL04	V <sub>DC</sub>	40	V
Maximum average forward rectified current	T <sub>tp</sub> = 109 °C		I <sub>F(AV)</sub>	1.1	А
Peak forward surge current 8.3 ms single half sine-wave			I <sub>FSM</sub>	40	А

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## **Maximum Thermal Resistance**

 $T_{amb} = 25 \ ^{\circ}C$ , unless otherwise specified

Parameter	Parameter		Value	Unit	
Thermal resistance junction to ambient air <sup>2)</sup>		$R_{ extsf{ heta}JA}$	180	K/W	
Maximum operating junction temperature		ТJ	125	°C	
Storage temperature range		T <sub>STG</sub>	- 55 to 150	°C	

<sup>2)</sup>Mounted on epoxy substrate with 3 x 3mm Cu pads ( $\geq$  40 µm thick)

## **Electrical Characteristics**

 $T_{amb}$  = 25 °C, unless otherwise specified

Parameter	Test condition	Part	Symbol	Тур.	Max	Unit
Instaneous forward voltage at 0.5 <sup>1)</sup>		SL02	V <sub>F</sub>	0.360	0.385	V
		SL03	V <sub>F</sub>	0.395	0.43	V
		SL04	V <sub>F</sub>	0.450	0.51	V
Typical instantaneous forward voltage	1.1 A	SL02	V <sub>F</sub>	0.420		V
	1.1 A	SL03	V <sub>F</sub>	0.450		V
	1.1 A	SL04	V <sub>F</sub>	0.530		V
Maximum DC reverse current at rated DC blocking voltage	T <sub>A</sub> = 25 °C	SL02	I <sub>R</sub>		250	μA
	T <sub>A</sub> = 100 °C	SL02	I <sub>R</sub>		8.0	mA
	T <sub>A</sub> = 25 °C	SL03	I <sub>R</sub>		130	μA
	T <sub>A</sub> = 100 °C	SL03	I <sub>R</sub>		6.0	mA
	T <sub>A</sub> = 25 °C	SL04	I <sub>R</sub>		20	μA
	T <sub>A</sub> = 100 °C	SL04	I <sub>R</sub>		6.0	mA

<sup>1)</sup> Pulse test: 300  $\mu$ s pulse width, 1 % duty cycle

# **Typical Characteristics** (T<sub>amb</sub> = 25 °C unless otherwise specified)

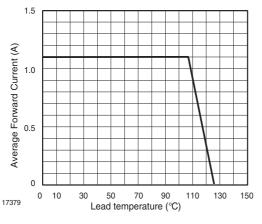


Figure 1. Forward Current Derating Curve

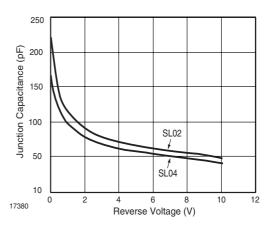


Figure 2. Typical Junction Capacitance



# SL02 to SL04

# **Vishay Semiconductors**

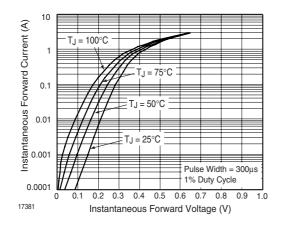


Figure 3. Typical Instantaneous Forward Characterisics - SL02

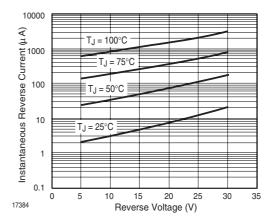


Figure 6. Typical Reverse Current Characteristics - SL03

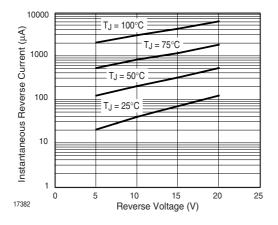


Figure 4. Typical Reverse Current Characteristics - SL02

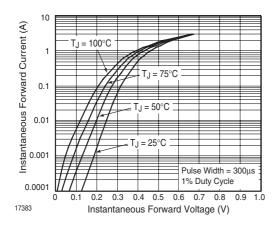


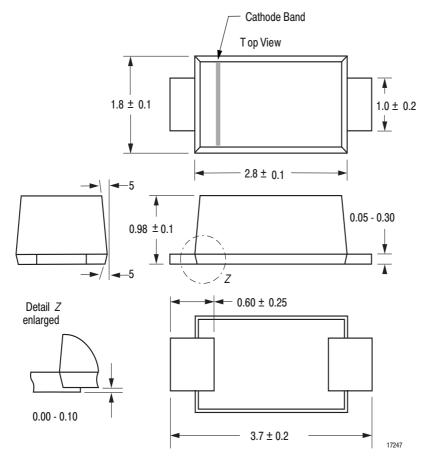
Figure 5. Typical Instantaneous Forward Characteristics - SL03

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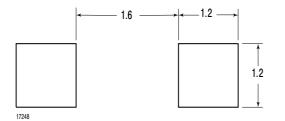


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# Package Dimensions in mm



#### **Mounting Pad Layout**





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## **Ozone Depleting Substances Policy Statement**

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operatingsystems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

#### We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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